

# PSMN1R6-30BL

# N-channel 30 V 1.9 mΩ logic level MOSFET in D2PAK

Rev. 1 — 22 March 2012

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

#### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V
$I_D$	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see Figure 2		-	-	306	W
Tj	junction temperature			-55	-	175	°C
Static cha	racteristics						
R <sub>DSon</sub> drain-source on-state resistance		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 °C;$ see <u>Figure 13</u> ; see <u>Figure 6</u>		-	2.21	2.6	mΩ
		$V_{GS} = 10 \text{ V; } I_D = 25 \text{ A; } T_j = 25 \text{ °C;}$ see <u>Figure 6</u>		-	1.58	1.9	mΩ
Dynamic o	haracteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 15 \text{ V};$		-	27	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15		-	101	-	nC
	ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 $\Omega$ ; unclamped		-	-	1.7	J

<sup>[1]</sup> Continuous current is limited by package.



# 2. Pinning information

Table 2. Pinning information

	-			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

<sup>[1]</sup> It is not possible to make connection to pin 2

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R6-30BL	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R6-30BL	PSMN1R6-30BL

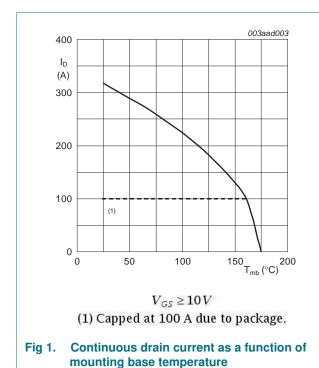
# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	30	V
$V_{DGR}$	drain-gate voltage	$T_j$ ≥ 25 °C; $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	[1]	-	100	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{M}}$	[1]	-	100	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; see Figure 3		-	1268	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	306	W
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drain of	diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	1268	Α
Avalanche rug	gedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le$ 30 V; $R_{GS}$ = 50 $\Omega$ ; unclamped		-	1.7	J

#### [1] Continuous current is limited by package.

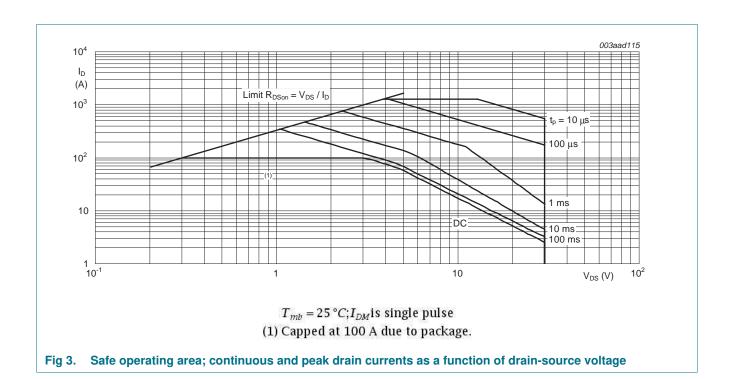


 $P_{der}^{O3aa16}$ 80
40  $0 = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$ 

Fig 2. Normalized total power dissipation as a function of mounting base temperature

PSMN1R6-30BL

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### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.49	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

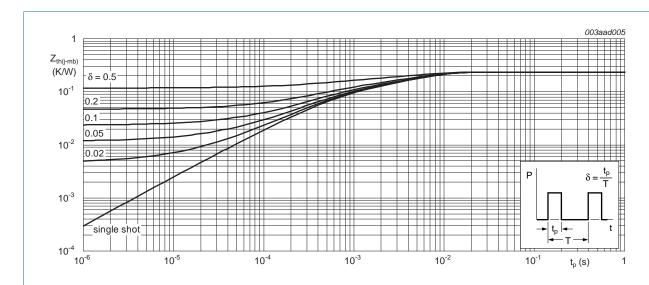


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

## 7. Characteristics

**Table 7. Characteristics** 

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	1.3	1.7	2.15	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 12	0.5	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 12	-	-	2.45	V
I <sub>DSS</sub> drain leakage current		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	5	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	150	μΑ
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R <sub>DSon</sub> drain-source on-state resis	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 13; see Figure 6	-	3	3.5	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 6	-	1.84	2.2	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 13; see Figure 6	-	2.21	2.6	mΩ	
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}; \text{see}$ Figure 6	-	1.58	1.9	mΩ	
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.98	-	Ω
Dynamic c	haracteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15	-	212	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	193	-	nC
		$I_D = 25 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 4.5 \text{ V}$ ;	-	101	-	nC
$Q_{GS}$	gate-source charge	see Figure 14; see Figure 15	-	33	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	20	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	13	-	nC
$Q_{GD}$	gate-drain charge		-	27	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.5	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	12493	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	2486	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1034	-	рF

 Table 7.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	104	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	163	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	174	-	ns
t <sub>f</sub>	fall time		-	87	-	ns
Source-dr	ain diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see Figure 17	-	0.77	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A}/\mu s;$	-	64	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	79	-	nC

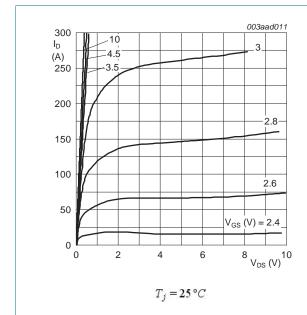


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

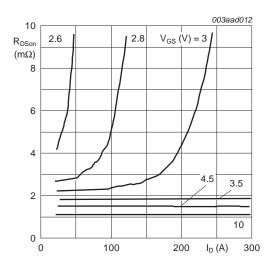


Fig 6. Drain-source on-state resistance as a function of drain current; typical values

 $T_j = 25 \,^{\circ}C$ 

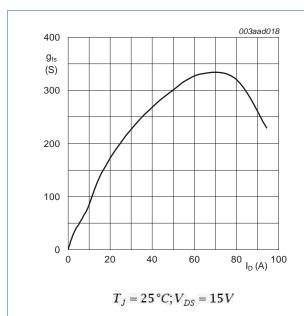


Fig 7. Forward transconductance as a function of drain current; typical values

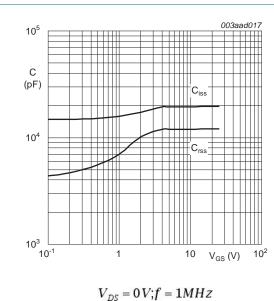
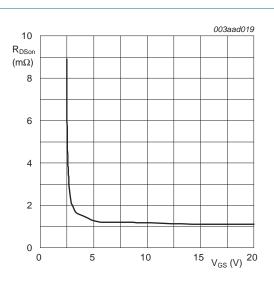
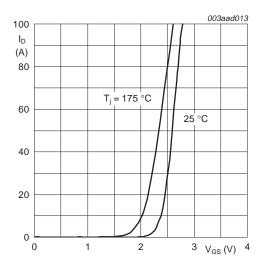


Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



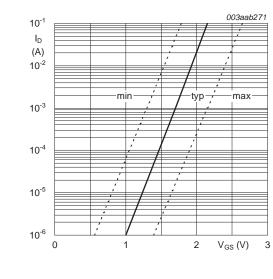
 $T_j=25\,^{\circ}C; I_D=25A$ 

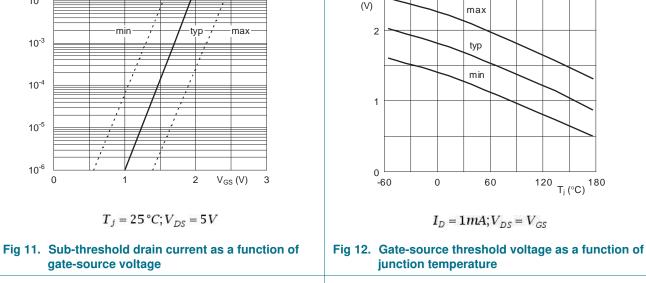
Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $V_{DS} > I_D \times R_{DSon}$ 

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values





3

V<sub>GS(th)</sub>

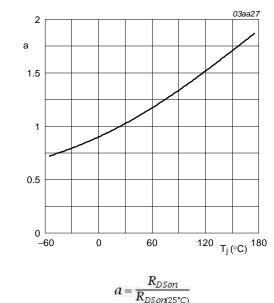


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

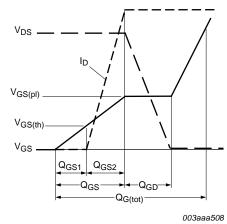


Fig 14. Gate charge waveform definitions

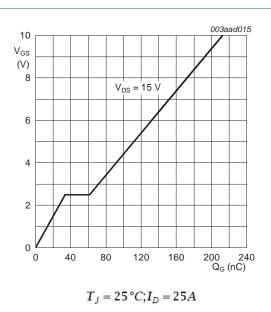
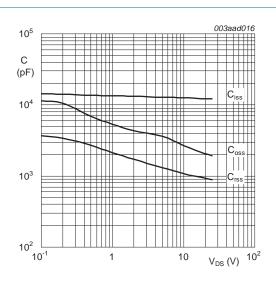
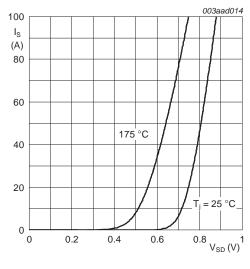


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $V_{GS} = 0 V$ 

Fig 17. Source current as a function of source-drain voltage; typical values

# 8. Package outline

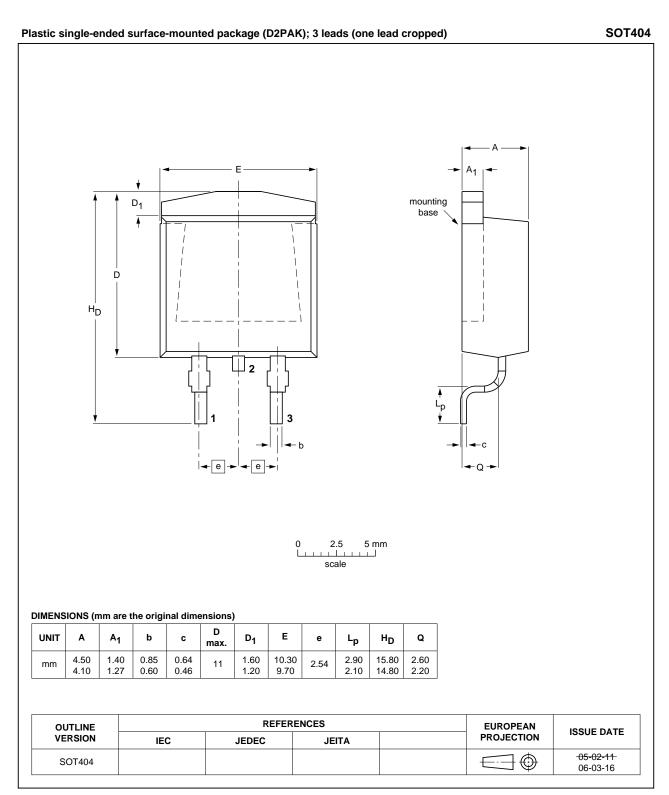


Fig 18. Package outline SOT404 (D2PAK)

# 9. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R6-30BL v.1	20120322	Product data sheet	-	-

### 10. Legal information

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Document status[1] [2]	Product status[3]	Definition
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Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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# PSMN1R6-30BL

## **Nexperia**

N-channel 30 V 1.9 m $\Omega$  logic level MOSFET in D2PAK

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